

Supporting Information

High performance thermoelectrics from low-cost and abundant CuS/CuI composites

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Additional information

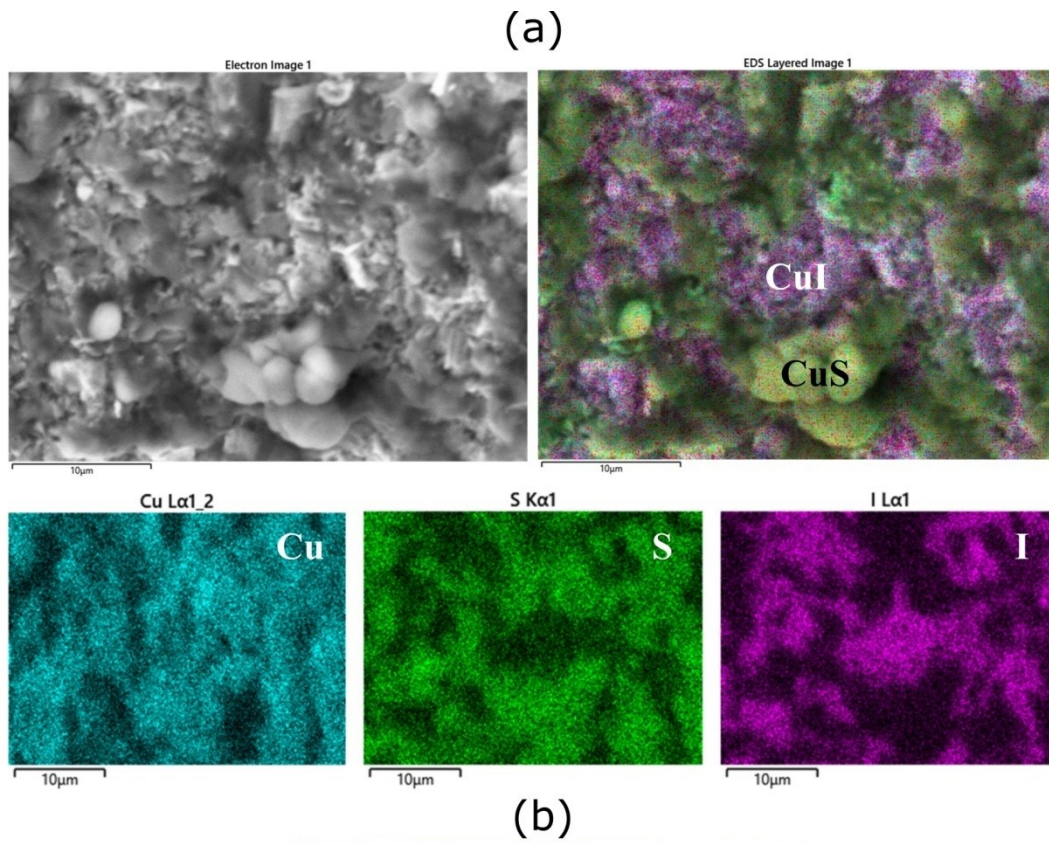
Employed basis sets listed in CRYSTAL17 input format, taken from <https://www.crystal.unito.it/basis-sets.php> (accessed 14/07/2022).

Copper	Sulphur
86-4111(41D)G_doll_2000	86-311G*_lichanot_1993
29 8	16 6
0 0 8 2.0 1.0	0 0 8 2.0 1.0
398000.0 0.000227	109211.0 0.0002520
56670.0 0.001929	16235.206 0.0019934
12010.0 0.01114	3573.0286 0.0111177
3139.0 0.05013	943.23811 0.0498945
947.2 0.17031	287.26179 0.1661455
327.68 0.3693	99.914226 0.3627018
128.39 0.4030	38.602137 0.4108787
53.63 0.1437	15.531224 0.1457875
0 1 6 8.0 1.0	0 1 6 8.0 1.0
1022.0 -0.00487 0.00850	281.22171 -0.0057780
238.9 -0.0674 0.06063	0.0081427
80.00 -0.1242 0.2118	67.106575 -0.0665855
31.86 0.2466 0.3907	0.0565570
13.33 0.672 0.3964	21.794135 -0.1203552
4.442 0.289 0.261	0.2039582
0 1 4 8.0 1.0	8.2097646 0.2741310
54.7 0.0119 -0.0288	0.3973328
23.26 -0.146 -0.0741	3.4178289 0.6463829
9.92 -0.750 0.182	0.3946313
4.013 1.031 1.280	1.5452225 0.2925792
0 1 1 1.0 1.0	0.1544345
1.582 1.0 1.0	0 1 3 6.0 1.0
0 1 1 0.0 1.0	4.3752432 -0.1750000 -

0.596 1.0 1.0	0.0613439
0 1 1 0.0 1.0	1.8096201 -0.5938952
0.150 1.0 1.0	0.1272251
0 3 4 10.0 1.0	0.6833985 0.8298996
48.54 0.031	1.2215893
13.55 0.162	0 1 1 0.0 1.0
4.52 0.378	0.2413 1.0 1.0
1.47 0.459	0 1 1 0.0 1.0
0 3 1 0.0 1.0	0.106 1.0 1.0
0.392 1.0	0 3 1 0. 1.
	0.383 1.0

Iodide LC_doll_1998	Iodide Mike Towler
253 5	53 11
INPUT	0 0 9 2.0 1.11463
7. 0 2 2 2 1 0	3796580.0 0.0000486
3.511200 83.113863 0	556463.0 0.000394
1.755600 5.201876 0	120030.0 0.00229
2.968800 82.811109 0	30877.7 0.011153
1.484400 3.379682 0	8938.77 0.046196
1.906600 10.304277 0	2853.41 0.153983
0.953300 7.588032 0	1013.04 0.3495
2.307500 -21.477936 0	403.42 0.4298
0 1 1 2.0 1.0 merged s and p	169.683 0.20006
2.130007 1.0 1.0	0 1 7 8.0 1.13163
0 1 1 0.0 1.0 merged s and p	10780.9 -0.000264
0.3245 1.0 1.0	0.0010711
0 1 1 0.0 1.0 merged s and p	2502.22 -0.00608 0.00978
0.1115 1.0 1.0	769.087 -0.0513 0.0575
0 2 1 5. 1	274.618 -0.147205 0.2194
2.432887 1.	111.365 0.1122 0.4605
0 0 1 0. 1	51.8482 0.5808 0.4568
1.770481 1.	25.1274 0.471 0.215
	0 1 6 8.0 1.15719
	230.902 0.00648 -0.0135
	91.8899 -0.0261 -0.0666
	38.3274 -0.3172 0.0089
	17.3859 -0.0365 0.8289
	8.1559 0.90233 1.3049
	3.88355 0.4588 0.443
	0 3 6 10.0 1.0
	407.397 0.013328
	121.623 0.0935
	45.6127 0.3035
	18.9877 0.470024
	8.4634 0.3103
	3.6279 0.054
	0 1 3 8.0 1.0
	9.05308 -2.3837 -0.0815
	4.9116 -0.5412 0.3104

2.3444 5.3892 0.719
0 1 1 7.0 1.0
1.179 1.0 1.0
0 3 3 10.0 1.0
6.7601 0.2229
2.7113 0.5615
1.1174 0.4214
0 3 1 0.0 1.0
0.4254 1.0
0 1 1 0.0 1.0
0.585 1.0 1.0
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0 1 1 0.0 1.0
0.0686 1.0 1.0



(b)

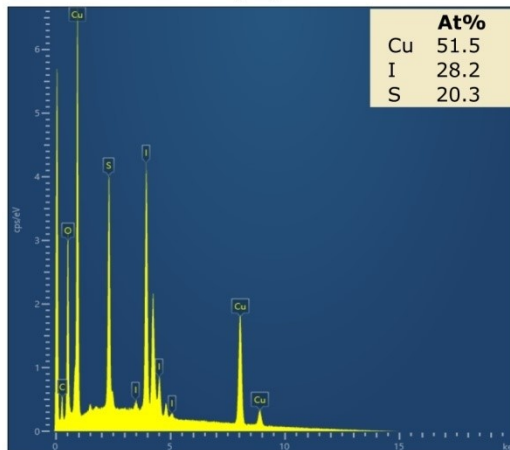


Figure S1. (a) SEM-EDX elemental mapping of a broken solid pellet of CuS:CuI (wt%)-1:4 sample. Images show coloured elemental mapping, (b) shows the composition of the same sample.

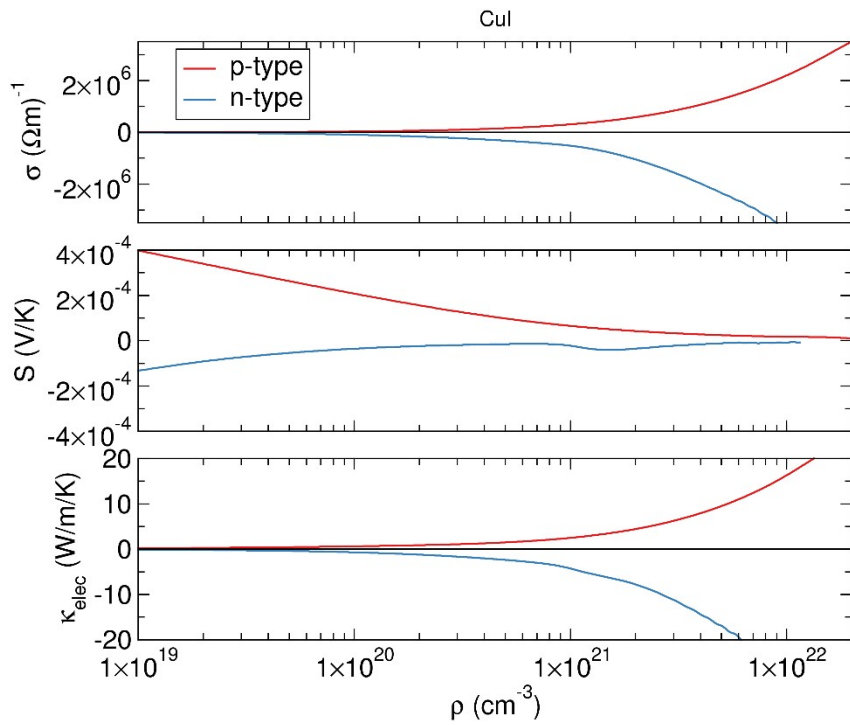
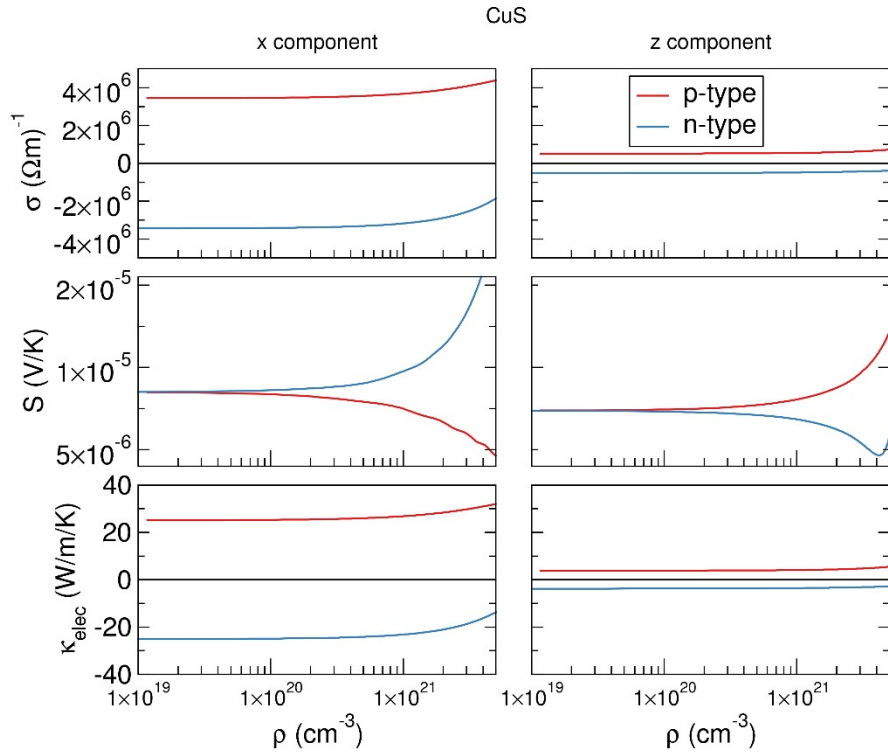


Figure S2. Calculated electrical conductivity (σ), Seebeck coefficient (S), and electronic part of the thermal conductivity (κ) as function of charge carrier concentration of CuS (top) and CuI (bottom) using the HSE functional.

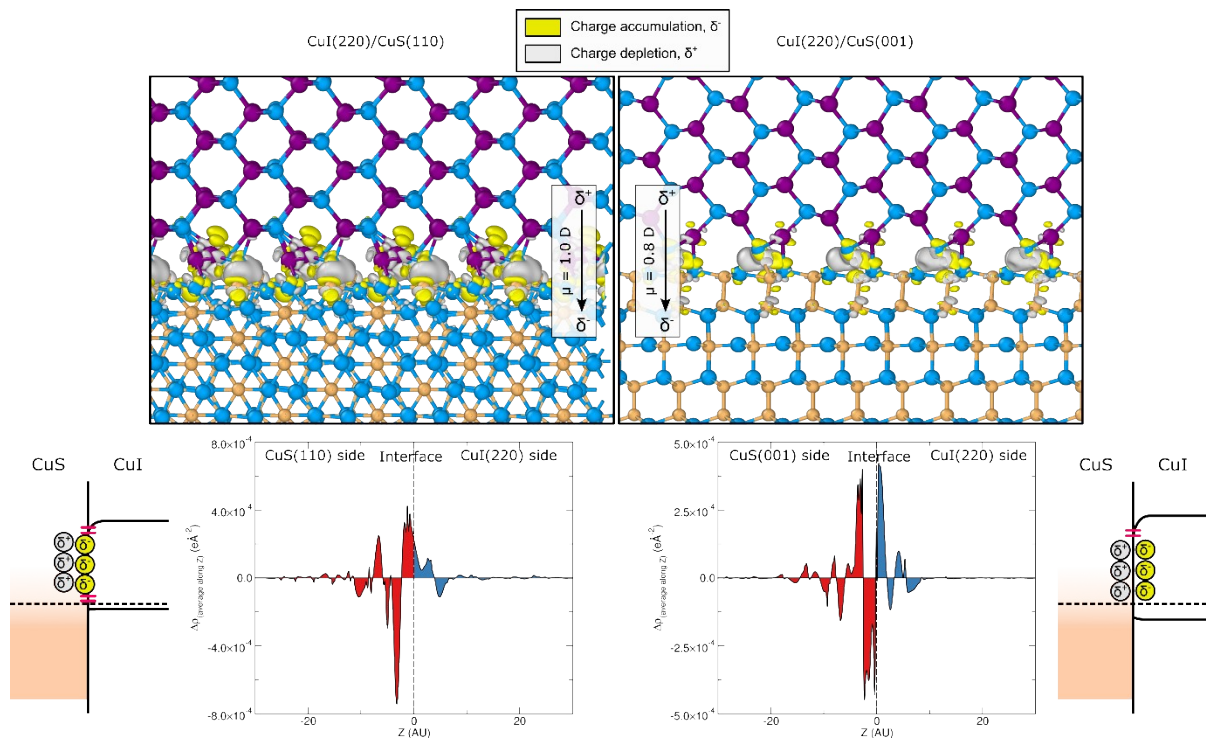


Figure S3. Calculated charge density difference (isosurface reported for a value of $0.002 \text{ e}\text{\AA}^{-3}$) together with the band alignment derived from the LPDOS analysis outlined in the main text, supplemented with the band bending mechanism elaborated through the planar averaged charge density.